

Norbert Kwietniewski

List of Publications by Year in descending order

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20
papers

130
citations

1478505

6
h-index

1281871

11
g-index

20
all docs

20
docs citations

20
times ranked

246
citing authors

#	ARTICLE	IF	CITATIONS
1	Performance of nanoimprinted and nanocoated optical label-free biosensor - nanocoating properties perspective. Optics and Lasers in Engineering, 2022, 153, 107009.	3.8	4
2	The interplay between damage- and chemical-induced isolation mechanism in Fe ⁺ -implanted AlGaIn/GaN HEMT structures. Materials Science in Semiconductor Processing, 2021, 127, 105694.	4.0	6
3	Ti and TiAl-based ohmic contacts to 4H-SiC. , 2020, , .		0
4	Influence of Atomic Layer Deposition Temperature on the Electrical Properties of Al ₂ ZrO ₂ /SiO ₂ /4H-SiC Metal-Oxide Semiconductor Structures. Physica Status Solidi (A) Applications and Materials Science, 2018, 215, 1700882.	1.8	6
5	Electrical properties of isotype and anisotype ZnO/4H-SiC heterojunction diodes. Applied Physics Letters, 2017, 110, .	3.3	7
6	Effects of ultra-shallow ion implantation from RF plasma onto electrical properties of 4H-SiC MIS structures with SiO _x /HfO _x and SiO _x Ny/HfO _x double-gate dielectric stacks. Microelectronic Engineering, 2017, 178, 116-121.	2.4	2
7	Electrical characterization of ZnO/4H-SiC n-p heterojunction diode. Physica Status Solidi (A) Applications and Materials Science, 2016, 213, 1120-1124.	1.8	5
8	Properties of silicon nitride thin overlays deposited on optical fibers – Effect of fiber suspension in radio frequency plasma-enhanced chemical vapor deposition reactor. Thin Solid Films, 2016, 603, 8-13.	1.8	4
9	Effect of Sample Elevation in Radio Frequency Plasma Enhanced Chemical Vapor Deposition (RF PECVD) Reactor on Optical Properties and Deposition Rate of Silicon Nitride Thin Films. Materials, 2014, 7, 1249-1260.	2.9	5
10	Fabrication and characterization of epitaxial 4H-SiC pn junctions. Proceedings of SPIE, 2014, , .	0.8	1
11	Technology and characterization of 4H-SiC p-i-n junctions. Proceedings of SPIE, 2013, , .	0.8	6
12	Selective deep wet etching of fused silica optical fibers for sensing applications. , 2013, , .		1
13	Silicon nitride (SiN _x) plasma deposition on optical fiber sensors: coating symmetry perspective. Proceedings of SPIE, 2013, , .	0.8	2
14	Electronic properties of BaTiO ₃ /4H-SiC interface. Materials Science and Engineering B: Solid-State Materials for Advanced Technology, 2011, 176, 301-304.	3.5	4
15	Microwave Conductivity of Very Thin Graphene and Metal Films. Journal of Nanoscience and Nanotechnology, 2011, 11, 3358-3362.	0.9	32
16	Measurements of Planar Metal-Dielectric Structures Using Split-Post Dielectric Resonators. IEEE Transactions on Microwave Theory and Techniques, 2010, , .	4.6	13
17	Stability of gold bonding and Ti/Au ohmic contact metallization to n-SiC in high power devices. , 2009, , .		1
18	Influence of surface cleaning effects on properties of Schottky diodes on 4H-SiC. Applied Surface Science, 2008, 254, 8106-8110.	6.1	21

#	ARTICLE	IF	CITATIONS
19	Improvement of electro-physical properties of ultra-thin PECVD silicon oxynitride layers by high-temperature annealing. <i>Vacuum</i> , 2008, 82, 1013-1019.	3.5	9
20	Planarization of Epitaxial SiC Trench Structures by Plasma Ion Etching. <i>Materials Science Forum</i> , 0, 821-823, 549-552.	0.3	1